

TOSHIBA Multichip Discrete Device

# HN7G01FE

Power Management Switch Applications  
 Driver Circuit Applications  
 Interface Circuit Applications

Unit: mm

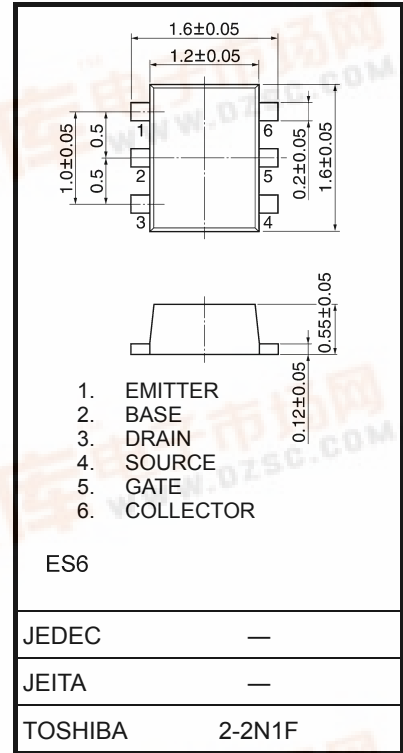
- Q1 (transistor): 2SA1955 equivalent
- Q2 (MOSFET): SSM3K03FE equivalent

### Q1 (Transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-15	V
Collector-emitter voltage	V <sub>CEO</sub>	-12	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-400	mA
Base current	I <sub>B</sub>	-50	mA

### Q2 (MOSFET) Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
Drain current	I <sub>D</sub>	50	mA



Weight: 0.003 g (typ.)

### Q1, Q2 Common Ratings (Ta = 25°C)

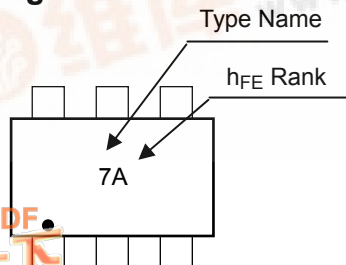
Characteristic	Symbol	Rating	Unit
Power dissipation	P (Note 1)	100	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

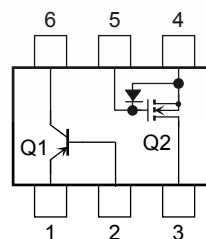
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

### Marking



### Pin Assignment (top view)



## Q1 (Transistor) Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -15\text{ V}, I_E = 0$	—	—	-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note 2)	$V_{CE} = -2\text{ V}, I_C = -10\text{ mA}$	300	—	1000	
Collector-emitter saturation voltage	$V_{CE(sat)}(1)$	$I_C = -10\text{ mA}, I_B = -0.5\text{ mA}$	—	-15	-30	mV
	$V_{CE(sat)}(2)$	$I_C = -200\text{ mA}, I_B = -10\text{ mA}$	—	-110	-250	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -200\text{ mA}, I_B = -10\text{ mA}$	—	-0.87	-1.2	V

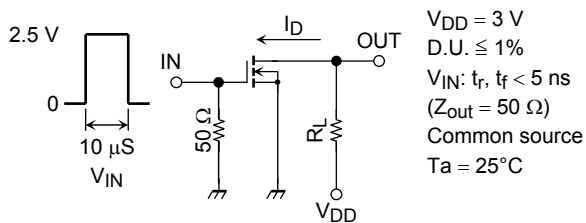
Note 2:  $h_{FE}$  classification A: 300~600, B: 500~1000

## Q2 (MOSFET) Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	$I_{GSS}$	$V_{GS} = 10\text{ V}, V_{DS} = 0$	—	—	1	$\mu\text{A}$	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 100\text{ }\mu\text{A}, V_{GS} = 0$	20	—	—	V	
Drain cutoff current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0$	—	—	1	$\mu\text{A}$	
Gate threshold voltage	$V_{th}$	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.7	—	1.3	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	25	50	—	mS	
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = 10\text{ mA}, V_{GS} = 2.5\text{ V}$	—	4	12	$\Omega$	
Input capacitance	$C_{iss}$	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	11.0	—	pF	
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	3.3	—	pF	
Output capacitance	$C_{oss}$	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	9.3	—	pF	
Switching time	Turn-on time	$t_{on}$	$V_{DD} = 3\text{ V}, I_D = 10\text{ mA}, V_{GS} = 0\sim 2.5\text{ V}$	—	0.16	—	$\mu\text{s}$
	Turn-off time	$t_{off}$	$V_{DD} = 3\text{ V}, I_D = 10\text{ mA}, V_{GS} = 0\sim 2.5\text{ V}$	—	0.19	—	

## Switching Time Test Circuit

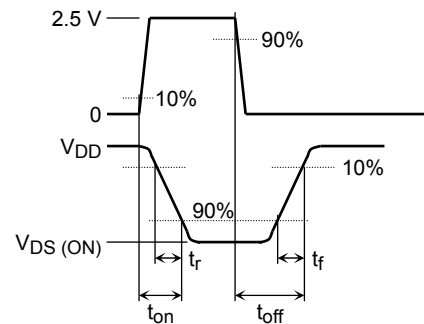
(a) Switching time test circuit



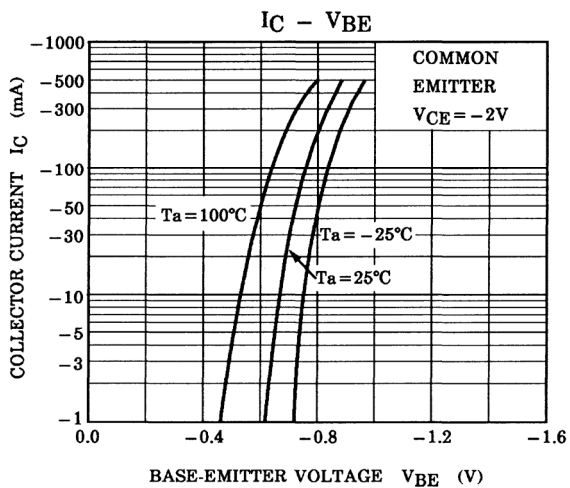
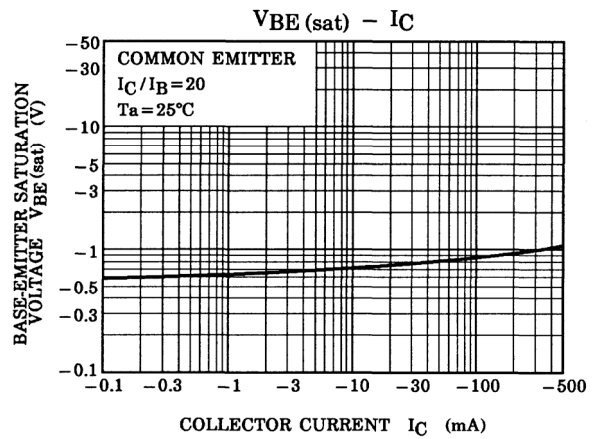
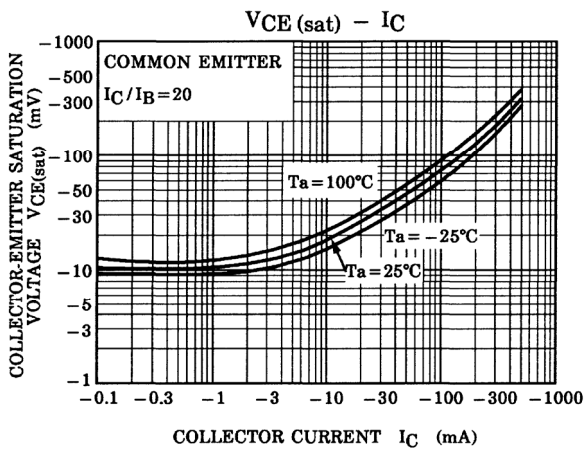
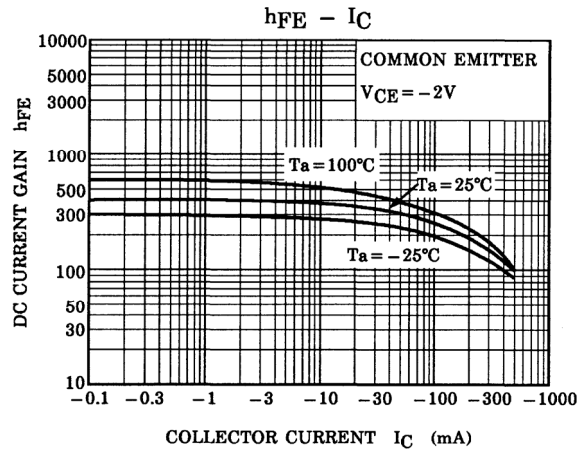
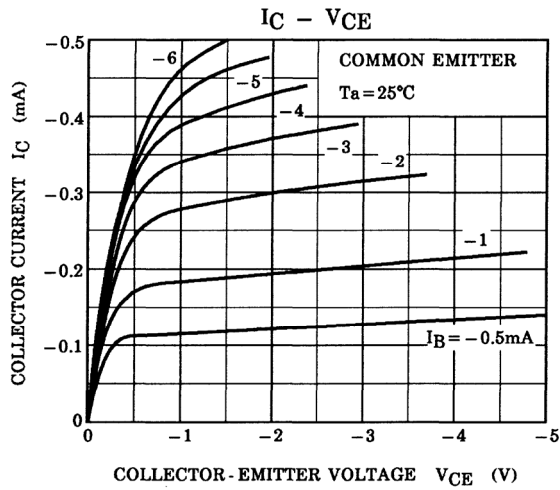
$V_{DD} = 3\text{ V}$   
 D.U.  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5\text{ ns}$   
 ( $Z_{out} = 50\text{ }\Omega$ )  
 Common source  
 $T_a = 25^\circ\text{C}$

(b)  $V_{IN}$   
 $V_{GS}$

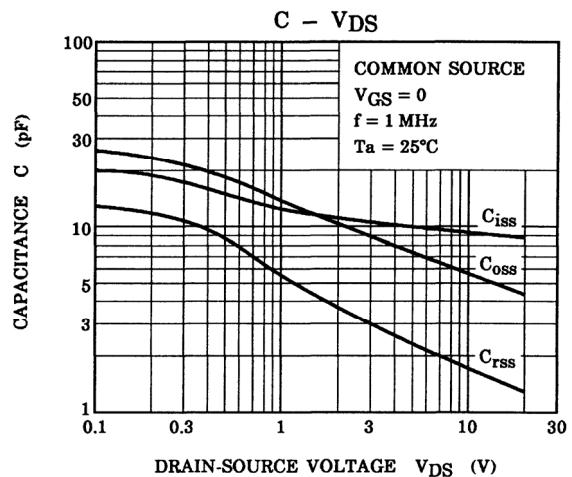
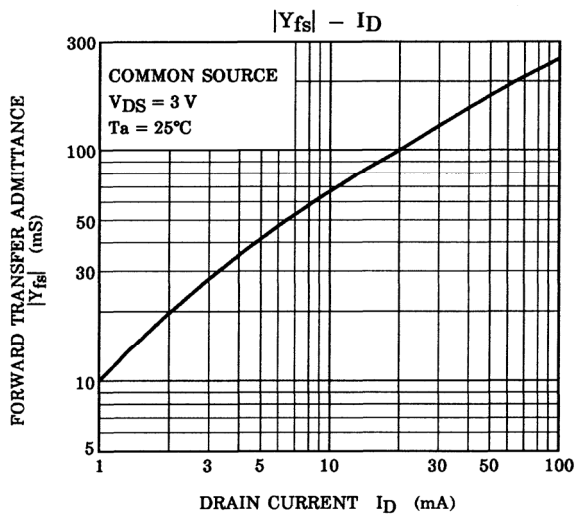
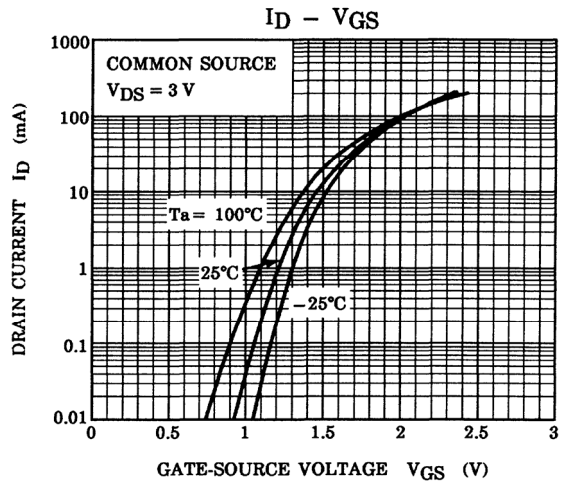
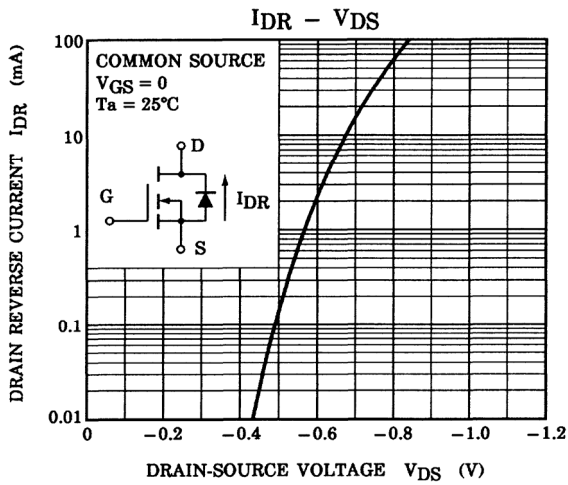
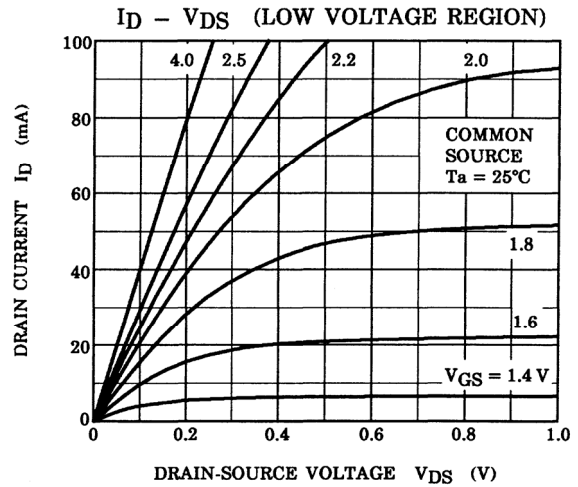
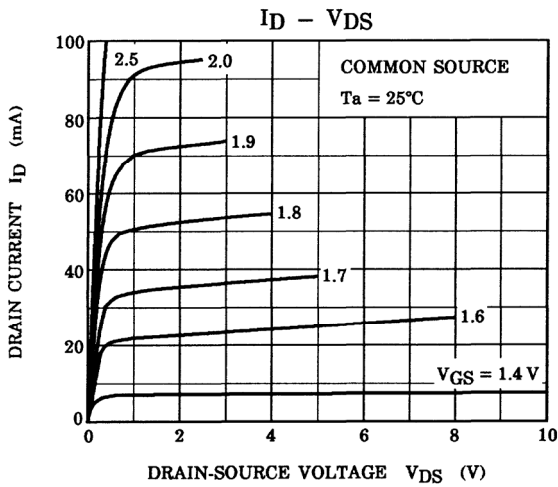
(c)  $V_{OUT}$   
 $V_{DS}$



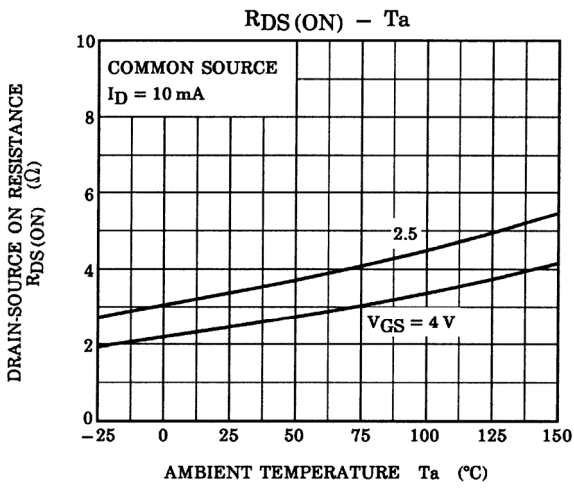
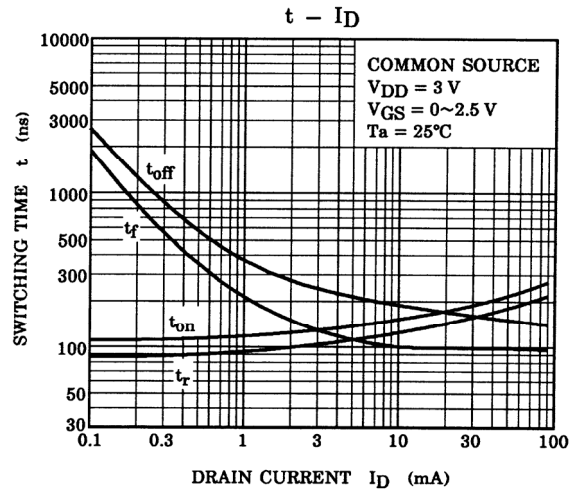
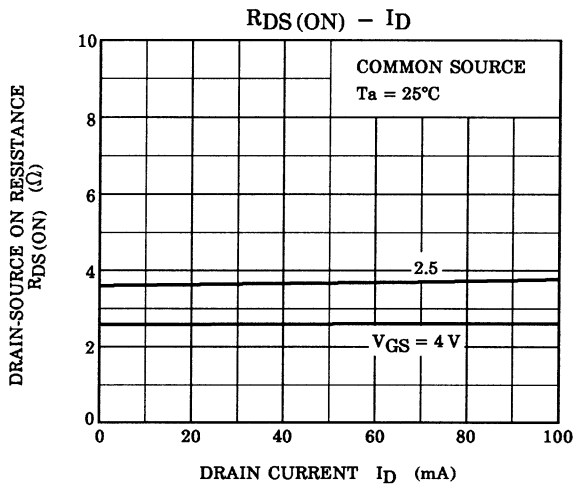
**Q1 (Transistor)**



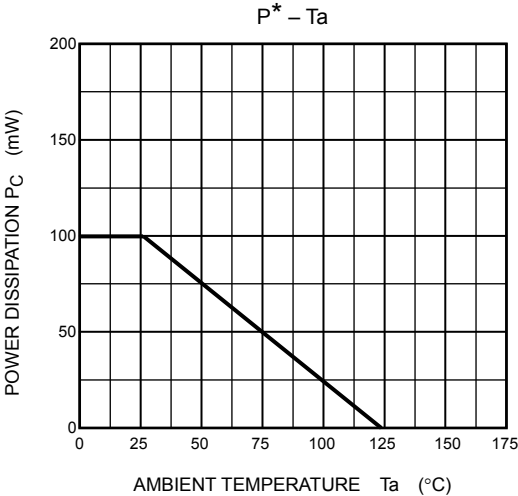
**Q2 (S-MOS)**



**Q2 (S-MOS)**



Q1, Q2 Common



\*:Total rating

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20070701-EN GENERAL

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